AMENDMENTS TO THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A method of forming a gate electrode in a semiconductor, comprising:

forming a polysilicon film and a metal tungsten silicide film sequentially on a semiconductor substrate;

performing an annealing process to crystallize the metal tungsten silicide film; and

tungsten silicide film and the polysilicon film performing an etching process to etch the tungsten silicide film and the polysilicon film under the tungsten silicide film using the same etching gas, thereby forming a gate electrode comprising the tungsten silicide film and the polysilicon film.

- 2. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 1, wherein the annealing process is one of an a rapid thermal process (RTP) annealing process and a furnace annealing process for crystallizing an amorphous metal tungsten silicide film to form a crystalline metal tungsten silicide film.
- 3. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 2, wherein comprising performing the RTP annealing process is performed at a temperature ranging from about 900°C to about 1000°C for a time period ranging from about 10 seconds to about 30 seconds in an ambient atmosphere of N₂ or NH₃ gas, and wherein performing the furnace annealing process is performed at a temperature ranging from about 850°C to about 1000°C for a time period ranging from about 5 minutes to about 30 minutes in an ambient of N₂ or NH₃ gas.

- 4. (Canceled)
- 5. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 1, wherein comprising performing the etching process is performed under a process condition for etching the polysilicon film.
- 6. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 5, wherein the etching process is a dry etching process which is performed, and comprising performing the etching process in an inductively coupled plasma chamber into which a mixture gas of Cl₂ gas and O₂ gas is introduced.
- 7. (Currently Amended) The method of forming a gate electrode in a semiconductor according to claim 1, wherein the etching process is a dry etching process which is performed, and comprising performing the etching process in an inductively coupled plasma chamber into which a mixture gas of Cl₂ gas and O₂ gas is introduced.
- 8. (Original) The method of forming a gate electrode in a semiconductor according to claim 1, where in the annealing process results in the etch rate of the crystallized metal silicide film being similar to that of the polysilicon film
- 9. (New) The method of forming a gate electrode in a semiconductor according to claim 1, comprising forming the tungsten silicide film by reacting SiH₄ or SiH₂Cl₂ with WF₆ at a stochiometric ratio of (SiH₄ or SiH₂Cl₂): WF₆ of 2.0 2.8.